



Features

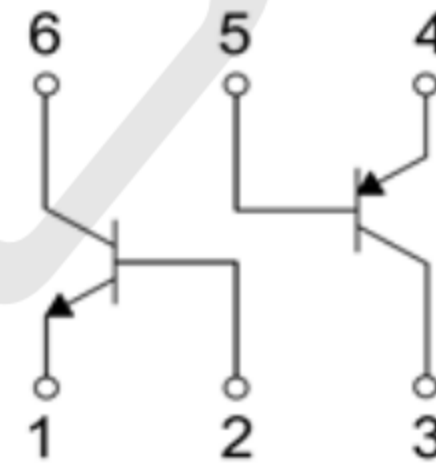
- Complementary Pair
- One 3904-Type NPN
One 3906-Type PNP
- Epitaxial Planar Die Construction
- Ideal for Low Power Amplification and Switching

Ordering Information

- Shipping Qty:3000/7inch Tape& Reel



Circuit Diagram



Absolute Maximum Ratings (Tamb=25°C unless otherwise specified)

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	60	V
V _{CEO}	Collector-Emitter Voltage	40	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current -Continuous	0.2	A
P _C	Collector Power Dissipation	0.2	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C



NPN 3904 Electrical Characteristics (TA=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 10\mu A, I_E = 0$	60		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 1mA, I_B = 0$	40		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 10\mu A, I_C = 0$	5		V
Collector cut-off current	I_{CBO}	$V_{CB} = 30V, I_E = 0$		0.05	μA
Collector cut-off current	I_{CEO}	$V_{CE} = 30V, I_B = 0$		0.5	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5V, I_C = 0$		0.05	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = 1V, I_C = 0.1mA$	40		
	$h_{FE(2)}$	$V_{CE} = 1V, I_C = 1mA$	70		
	$h_{FE(3)}$	$V_{CE} = 1V, I_C = 10mA$	100	300	
	$h_{FE(4)}$	$V_{CE} = 1V, I_C = 50mA$	60		
	$h_{FE(5)}$	$V_{CE} = 1V, I_C = 100mA$	30		
Collector-emitter saturation voltage	$V_{CE(sat)1}$	$I_C = 10mA, I_B = 1mA$		0.2	V
	$V_{CE(sat)2}$	$I_C = 50mA, I_B = 5mA$		0.3	V
Base-emitter saturation voltage	$V_{BE(sat)1}$	$I_C = 10mA, I_B = 1mA$	0.65	0.85	V
	$V_{BE(sat)2}$	$I_C = 50mA, I_B = 5mA$		0.95	V
Transition frequency	f_T	$V_{CE} = 20V, I_C = 20mA, f = 100MHz$	300		MHz
Noise figure	NF	$V_{CE} = 5V, I_C = 0.1mA, f = 1KHz, R_g = 1K\Omega$		5	dB
Output capacitance	C_{ob}	$V_{CB} = 5V, I_E = 0, f = 1MHz$		4	pF
Delay time	t_d	$V_{CC} = 3V, V_{BE} = 0.5V$		35	nS
Rise time	t_r	$I_C = 10mA, I_{B1} = -I_{B2} = 1mA$		35	nS
Storage time	t_s	$V_{CC} = 3V, I_C = 10mA$		200	nS
Fall time	t_f	$I_{B1} = -I_{B2} = 1mA$		50	nS



Absolute Maximum Ratings (Tamb=25°C unless otherwise specified)

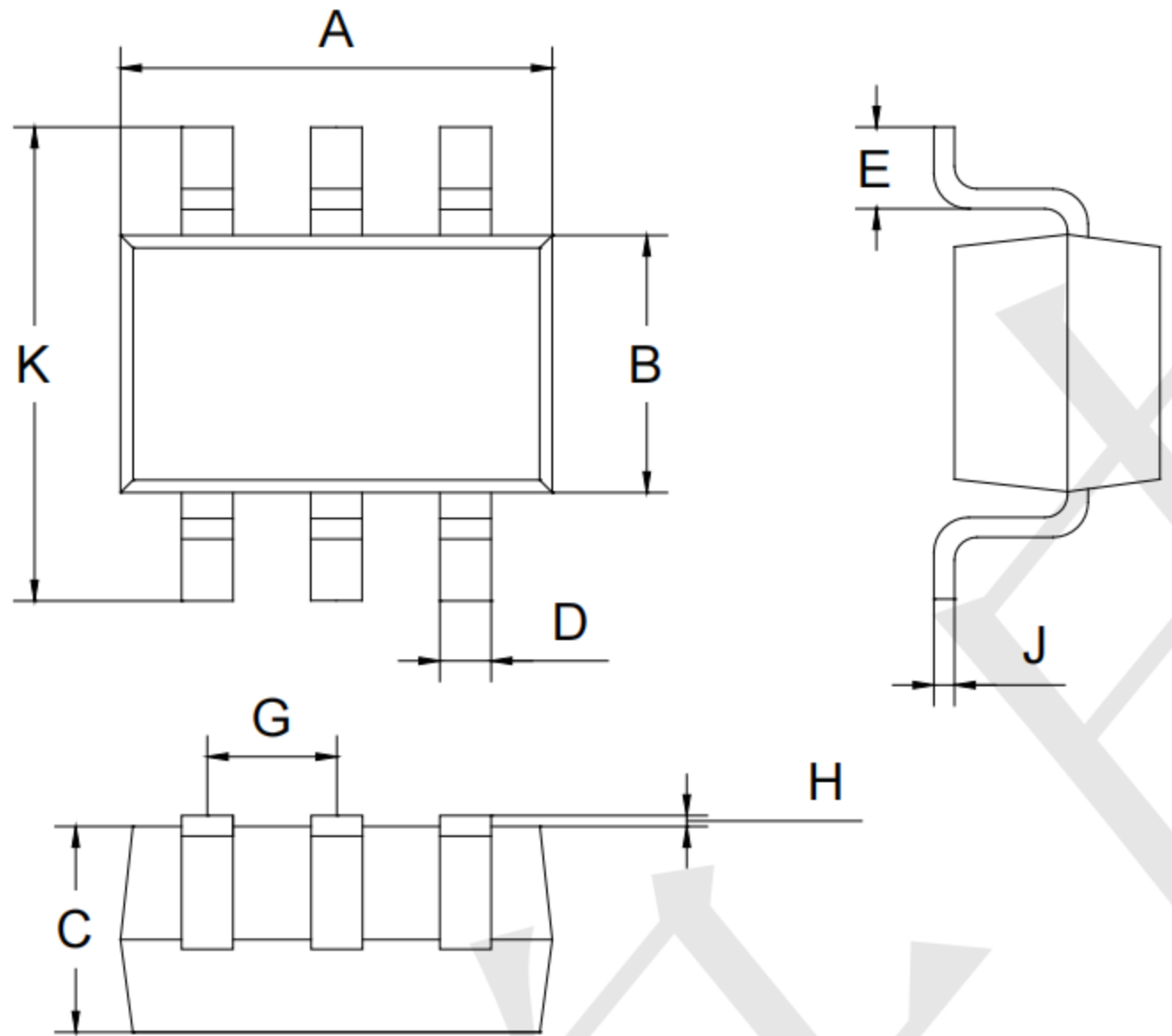
Symbol	Parameter	Value	Units
V _{CB0}	Collector-Base Voltage	-40	V
V _{CEO}	Collector-Emitter Voltage	-40	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-0.2	A
P _C	Collector Power Dissipation	0.2	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C

PNP 3906 Electrical Characteristics (TA=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-10μA, I _E =0	-40			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-1mA, I _B =0	-40			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-10μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-30V, I _E =0			-0.05	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0			-0.05	μA
DC current gain	h _{FE(1)}	V _{CE} =-1V, I _C =-0.1mA	60			
	h _{FE(2)}	V _{CE} =-1V, I _C =-1mA	80			
	h _{FE(3)}	V _{CE} =-1V, I _C =-10mA	100		300	
	h _{FE(4)}	V _{CE} =-1V, I _C =-50mA	60			
	h _{FE(5)}	V _{CE} =-1V, I _C =-100mA	30			
Collector-emitter saturation voltage	V _{CE(sat)1}	I _C =-10mA, I _B =-1mA			-0.25	V
	V _{CE(sat)2}	I _C =-50mA, I _B =-5mA			-0.4	V
Base-emitter saturation voltage	V _{BE(sat)1}	I _C =-10mA, I _B =-1mA	-0.65		-0.85	V
	V _{BE(sat)2}	I _C =-50mA, I _B =-5mA			-0.95	V
Transition frequency	f _T	V _{CE} =-20V, I _C =-10mA, f=100MHz	250			MHz
Collector output capacitance	C _{ob}	V _{CB} =-5V, I _E =0, f=1MHz			4.5	pF
Noise figure	NF	V _{CE} =-5V, I _C =-0.1mA, f=1KHz, R _g =1KΩ			4	dB
Delay time	t _d	V _{CC} =-3V, V _{BE} =-0.5V			35	nS
Rise time	t _r	I _C =-10mA, I _{B1} =-I _{B2} =-1mA			35	nS
Storage time	t _s	V _{CC} =-3V, I _C =-10mA			225	nS
Fall time	t _f	I _{B1} =-I _{B2} =-1mA			75	nS

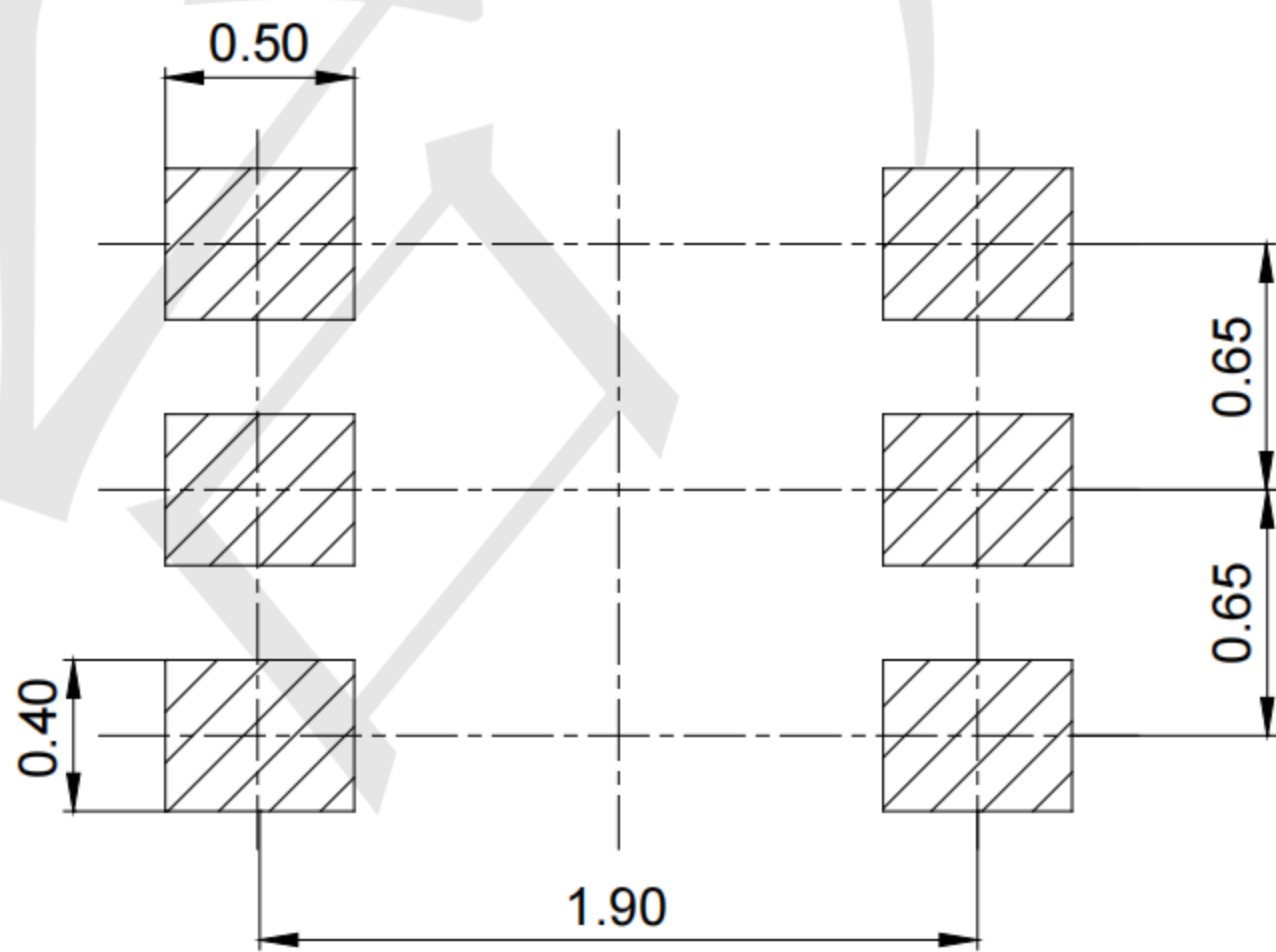


Outline Drawing - SOT363 (unit: mm)



SOT-363		
Dim	Min	Max
A	2.00	2.20
B	1.15	1.35
C	0.85	1.05
D	0.15	0.35
E	0.25	0.40
G	0.60	0.70
H	0.02	0.10
J	0.05	0.15
K	2.20	2.40

Mounting Pad Layout-SOT363 (unit: mm)



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